

EAST - [10720810.wsp:1]

File View Edit Tools Window Help

Drafts
Pending
Active
L1: (20742) nonvolatile near memory
L2: (26) 1 and (insulation and cap and floa
L3: (91) 1 and (insulat\$2 and cap and floa
Failed
Saved
Favorites
Tagged (0)
UDC
Queue
Trash

Browse Queue Clear

DBs: USPAT:EPO, JPO, DERWENT:IBM_TDB

Default operator: OR

Plurals

Highlight all hit terms initially

1 and (insulat\$2 and cap and floating adj gate)

BRST... IS&F Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6677638 B2	20040113	23	Nonvolatile memory device and method for fabricating the same	257/314	257/315; 257/324;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6657248 B1	20031202	42	Semiconductor device having groove isolation structure and gate oxide films with	257/306	257/506
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6646303 B2	20031111	59	Nonvolatile semiconductor memory device and a method of manufacturing the same	257/321	257/315; 257/316;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6642552 B2	20031104	39	Inductive storage capacitor	257/195	257/281; 257/531
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6593624 B2	20030715	29	Thin film transistors with vertically offset drain regions	257/344	257/324; 257/347;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6583471 B1	20030624	48	Semiconductor device having first and second insulating films	257/350	257/59; 257/72
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6576537 B2	20030610	9	Flash memory cell and method for fabricating a flash memory cell	438/594	438/263; 438/264
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6573567 B1	20030603	39	IC card	257/358	257/E23.176; 361/737;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6573132 B1	20030603	18	Method for fabricating a semiconductor device having contacts self-aligned with a	438/211	257/410; 438/184;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6570215 B2	20030527	9	Nonvolatile memories with floating gate spacers, and methods of fabrication	257/315	257/E21.682; 257/E27.103;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6563736 B2	20030513	14	Flash memory structure having double celled elements and method for fabricating	365/185.18	257/317; 365/185.02